

IN THE CLAIMS:

1. (Currently Amended) A pattern forming method, comprising the steps of:
forming a first resist pattern containing a photo-acid generating agent ~~on~~ as a layer
above a substrate;
irradiating light ~~to~~ over an exposed surface of the first resist pattern;
coating a resist film containing a cross-linking agent, which reacts with acid, ~~on the~~
~~substrate~~ over the first resist pattern after said irradiation of ~~the light in a state where it covers~~
~~the first resist pattern~~;
~~causing a cross-linking reaction at an interface between the first resist pattern and the~~
~~resist film to grow~~ growing a cross-linked layer at an interface between the first resist pattern
and the resist film; and
thereby forming a second resist pattern ~~made~~ comprised of the cross-linked layer and
the first resist pattern.
2. (Original) A pattern forming method according to claim 1, wherein the light is one
selected from the group consisting of ArF excimer laser light and KrF excimer laser light.
3. (Original) A pattern forming method according to claim 1, wherein a base resin of a
resist material forming the first resist pattern containing the photo-acid generating agent is
one selected from the group consisting of methacrylic resin and cycloolefin resin.
4. (Original) A pattern forming method according to claim 1, wherein a base resin of the
resist film containing the cross-linking agent, which reacts with the acid, is one selected from
the group consisting of polyvinyl alcohol system resin, polyacrylic acid system resin, and